

Form PTO-1449		U.S. DEPARTMENT OF COMMERCE PATENT AND TRADEMARK OFFICE		ATTY. DOCKET NO. MI22-2157		SERIAL NO. Unknown <i>10/288,748</i>		
LIST OF ART CITED BY APPLICANT (Use several sheets if necessary)				APPLICANT: Don Carl Powell				
				FILING DATE <i>10/17/03</i> Filed Herewith		GROUP <i>2891</i> Unknown		
U.S. PATENT DOCUMENTS								
Examiner's Initials		Document Number	Date	Name	Class	Subclass	Filing Date if Appropriate	
<i>CME</i>	AA	5,739,066	04/14/98	Pan	<i>438</i>	<i>595</i>	—	
<i>CME</i>	AB	6,114,735	09/05/00	Batra et al.	<i>257</i>	<i>411</i>	—	
<i>CME</i>	AC	6,335,254 B1	01/01/02	Trivedi	<i>438</i>	<i>305</i>	—	
	AD							
	AE							
	AF							
	AG							
	AH							
	AI							
FOREIGN PATENT DOCUMENTS								
		Document Number	Date	Country	Class	Subclass	Translation	
							Yes	No
	AJ							
	AK							
	AL							
OTHER REFERENCES (including Author, Title, Date, Pertinent Pages, Etc.)								
<i>CME</i>	AM		Hiura et al., <i>Integration Technology of Polymetal (WWSiN/Poly-Si) Dual Gate CMOS for 1 Gbit DRAMs</i>					
			and Beyond, IEEE 398-392 (September 1998).					
<i>CME</i>	AN		Kawada et al., <i>Water Vapor Generator by Catalytic Reactor</i> (pre-February 2001).					
<i>CME</i>	AO		Lee et al., <i>In-situ Barrier Formation for High Reliable W/barrier/poly-Si Gate Using Denudation of WN, on</i>					
			Polycrystalline Si, IEEE 385-388 (September 1998).					
EXAMINER <i>C. Evers</i>		DATE CONSIDERED <i>4-27-05</i>						
<small>*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.</small>								

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Document Number	Date	Country	Class	Subclass	Translation		
					Yes	No	

OTHER REFERENCES (including Author, Title, Date, Pertinent Pages, Etc.)		
<i>CME</i>	AM	Nagahama et al., <i>Wet Hydrogen Oxidation System for Metal gate LSI's</i> (pre-February 2001).
<i>CME</i>	AN	Ohnishi et al., <i>Improving gate oxide integrity (GOI) of a W/WNx/dual-poly Si stacked-gate by using Wet-Hydrogen oxidation in 0.14-μm CMOS devices</i> , IEEE 397-400 (September 1998).
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